- 12. The method of Claim 11, wherein said flushing of said etching chamber is carried out via said auxiliary chamber, said auxiliary chamber being evacuated after etching and prior to refilling the auxiliary chamber.
- 13. The method of Claim 11, further comprising shutting off said at least one of a second etchant and a second etch catalyst to said chamber when said auxiliary chamber is connected to said etching chamber.
  - 14. The method of Claim 11, wherein the first etchant is hydrogen flouride.
  - 15. An installation for etching a substrate, comprising:

an etching chamber for a substrate, the etching chamber having an opening;

a piping system coupled to the opening and providing for at least a first fluid feed and a second fluid feed, the first and second fluid feeds configured to separately provide etching fluids to the etching chamber via the piping system; and

an auxiliary chamber positioned within the piping system and having an inlet and an outlet, wherein the inlet includes a controllable shut-off valve and is in communication with the first fluid feed, wherein the outlet includes a controllable shut-off valve and is in communication with the etching chamber, and wherein only one of said shut-off valves is open at a time.

- 16. The installation of Claim 15, wherein the piping system includes a bypass line for bypassing said auxiliary chamber.
- 17. The installation of Claim 15, wherein said etching chamber is connected to a vacuum pump.
- 18. The installation of Claim 15, wherein the piping system includes a valve coupled to the second fluid feed.
- 19. The installation of Claim 15, wherein said etching chamber is of a plastic material and is configured to withstand a reduced pressure in said etching chamber.
- 20. The installation of Claim 19, wherein said plastic material comprises polyvinylidene fluoride.